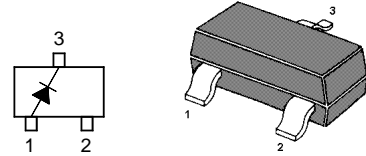


MMBD301

Silicon Epitaxial Planar Schottky Barrier Diode

Features

- Low forward voltage
- Low Reverse current
- Very low capacitance
- Fast switching



Marking Code: **43**
SOT-23 Plastic Package

Applications

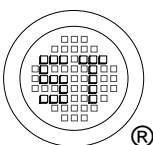
- High efficiency UHF and VHF detector applications
- Fast switching RF and digital applications

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	30	V
Average Rectified Forward Current	$I_{F(AV)}$	200	mA
Power Dissipation	P_{tot}	200	mW
Operating Junction Temperature Range	T_j	- 55 to + 125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

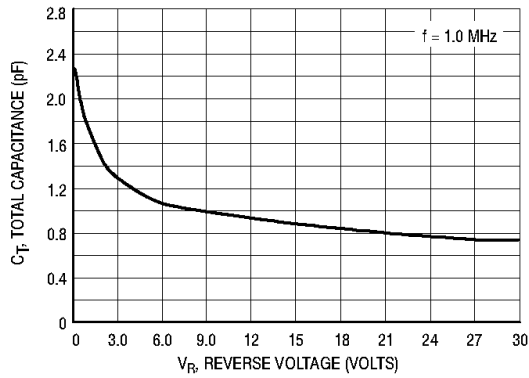
Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 1\text{ mA}$	V_F	-	0.45	V
at $I_F = 10\text{ mA}$	V_F	-	0.6	V
Reverse Breakdown Voltage at $I_R = 10\text{ }\mu\text{A}$	$V_{(BR)R}$	30	-	V
Reverse Current at $V_R = 25\text{ V}$	I_R	-	200	nA
Total Capacitance at $V_R = 15\text{ V}$, $f = 1\text{ MHz}$	C_T	-	1.5	pF



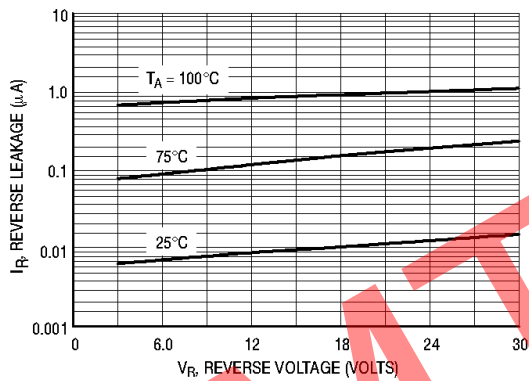
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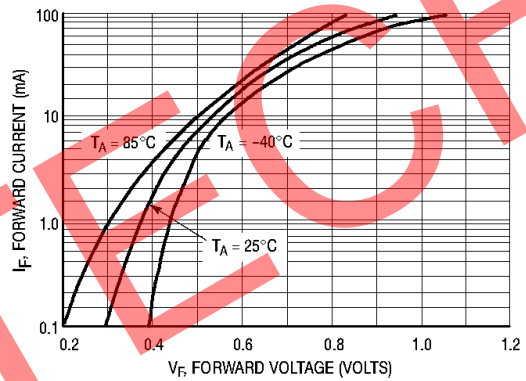
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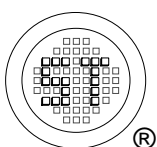
Total Capacitance



Reverse Leakage



Forward Voltage



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Dated : 30/07/2009